

## Features

- 100V/3.4A,  
 $R_{DS(ON)} = 76m\Omega(Typ.)@V_{GS}=10V$   
 $R_{DS(ON)} = 94m\Omega(Typ.)@V_{GS}=4.5V$
- Excellent  $Q_G \times R_{DS(on)}$  product(FOM)
- SGT Technology
- Low Capacitance to Minimize Driver Losses
- Fast Switching Speed

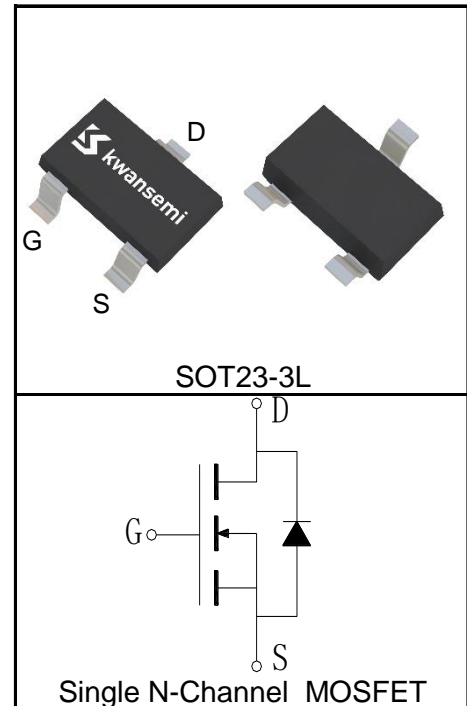
## Applications

- Load Switch



Halogen-Free

## Pin Description



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	100	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$I_S$	Diode Continuous Forward Current	$T_A=25^\circ\text{C}$ 1.3	A
<b>Mounted on Large Heat Sink</b>			
$I_{DP}^{①}$	300 $\mu\text{s}$ Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ 13	A
$I_D^{②}$	Continuous Drain Current( $V_{GS}=10V$ )	$T_A=25^\circ\text{C}$ 3.4	A
		$T_A=70^\circ\text{C}$ 2.7	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 1.25	W
		$T_A=70^\circ\text{C}$ 0.8	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	60	$^\circ\text{C/W}$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	100	$^\circ\text{C/W}$
<b>Drain-Source Avalanche Ratings</b>			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	TBD	mJ

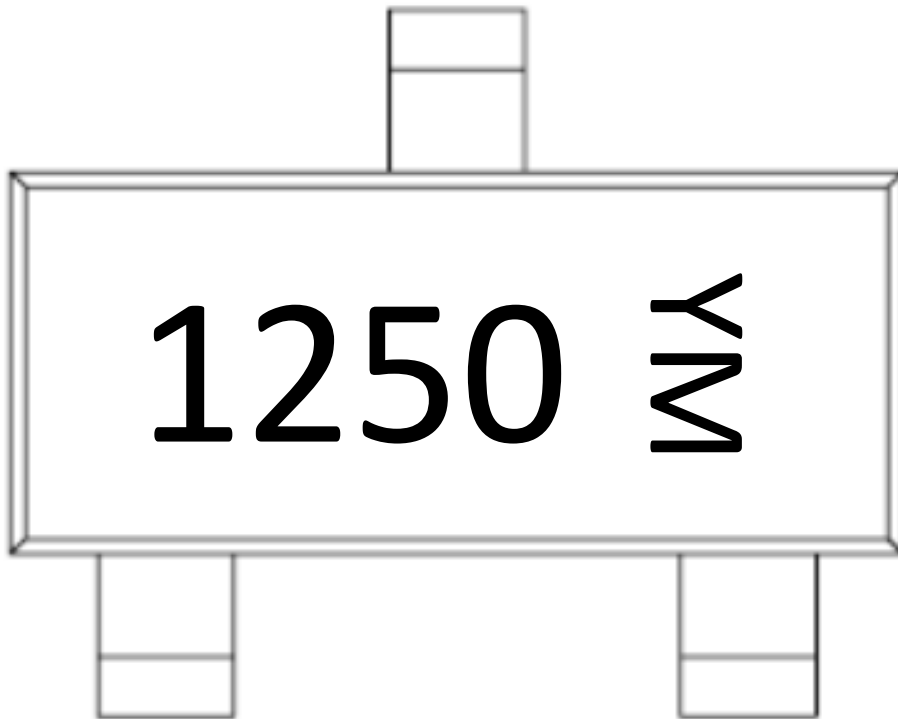
**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS1250EAT			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1.2	1.6	2.3	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=3A$		76	90	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=2A$		94	120	$m\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=3A, V_{GS}=0V$		0.89	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=3A, di_{SD}/dt=100A/\mu s$		16		ns
$Q_{rr}$	Reverse Recovery Charge			35		nC
<b>Dynamic Characteristics<sup>(6)</sup></b>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1		$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=50V,$ Frequency=1.0MHz		375		pF
$C_{oss}$	Output Capacitance			70		
$C_{rss}$	Reverse Transfer Capacitance			20		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=50V, I_{DS}=3A,$ $V_{GEN}=10V, R_G=6\Omega$		8		ns
$t_r$	Turn-on Rise Time			15		
$t_{d(OFF)}$	Turn-off Delay Time			22		
$t_f$	Turn-off Fall Time			10		
<b>Gate Charge Characteristics<sup>(6)</sup></b>						
$Q_g$	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V,$ $I_{DS}=3A$		9		nC
$Q_{gs}$	Gate-Source Charge			1.8		
$Q_{gd}$	Gate-Drain Charge			1.7		

- Notes:
- ① Pulse width limited by safe operating area.
  - ② Calculated continuous current based on maximum allowable junction temperature.
  - ③ When mounted on 1 inch square copper board,  $t \leq 10$ sec. The value in any given application depends on the user's specific board design.
  - ④ Limited by  $T_{Jmax}$ . Starting  $T_J = 25^\circ C$ .
  - ⑤ Pulse test; Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
  - ⑥ Guaranteed by design, not subject to production testing.

**Ordering and Marking Information**

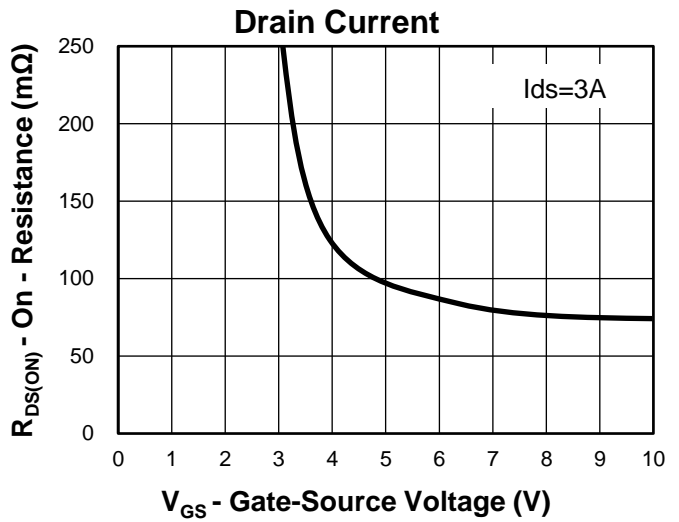
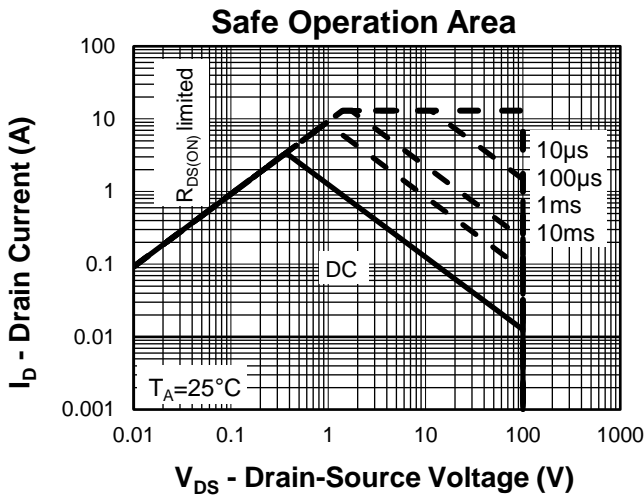
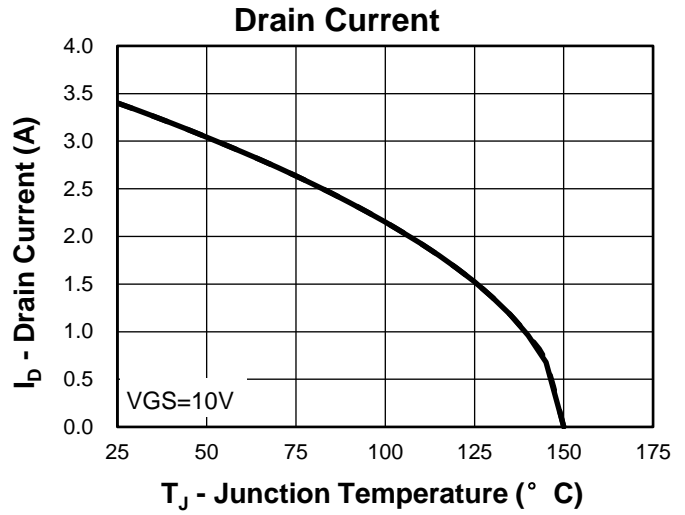
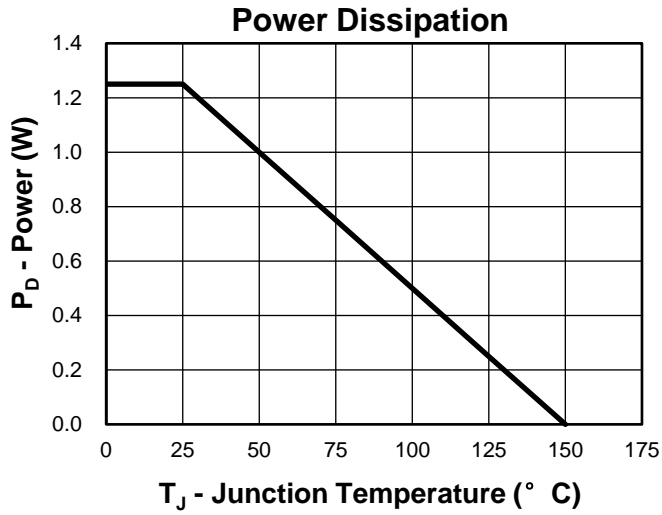
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS1250EAT	SOT23-3L	Tape&Reel	3000	7"	8mm



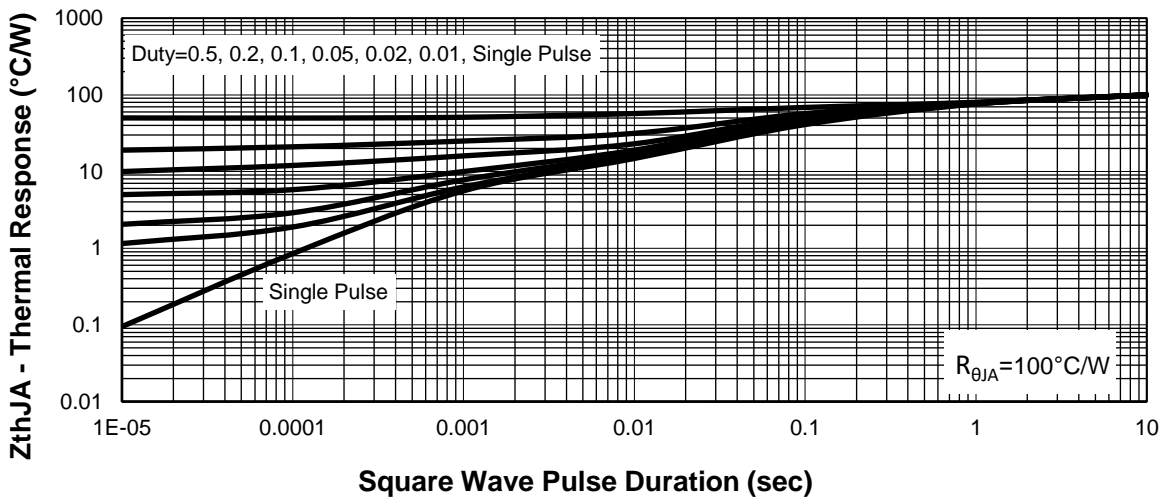
Y =Year,2017-A,2018-B,etc.

M =Month,Jan-1,Feb-2,....Sep-9,Oct-A,Nov-B,Dec-C.

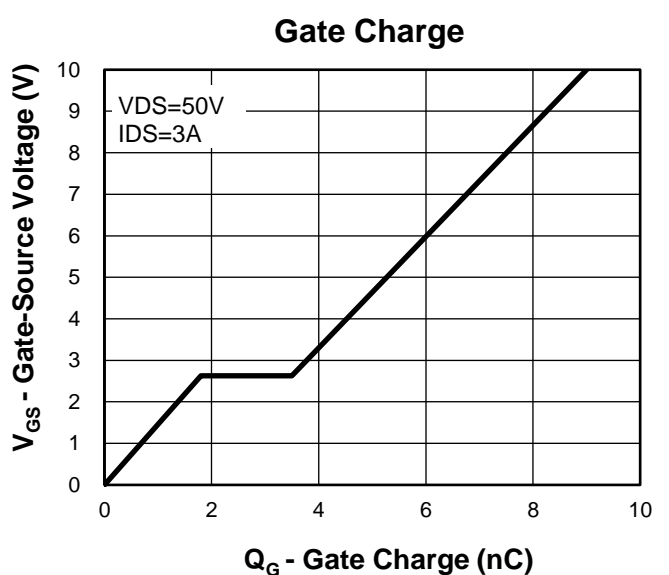
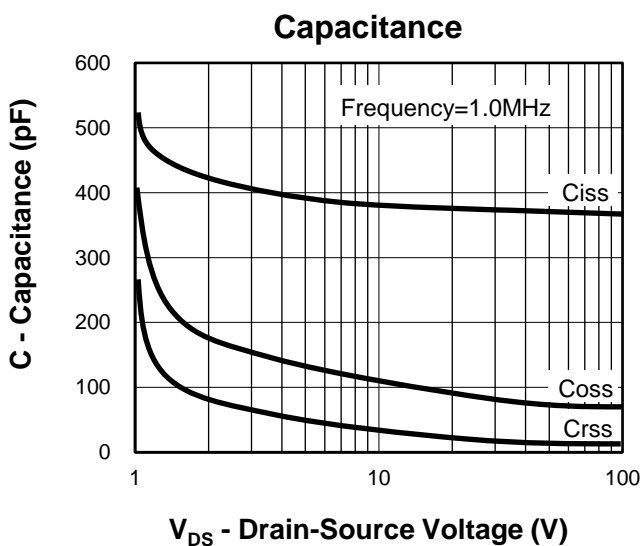
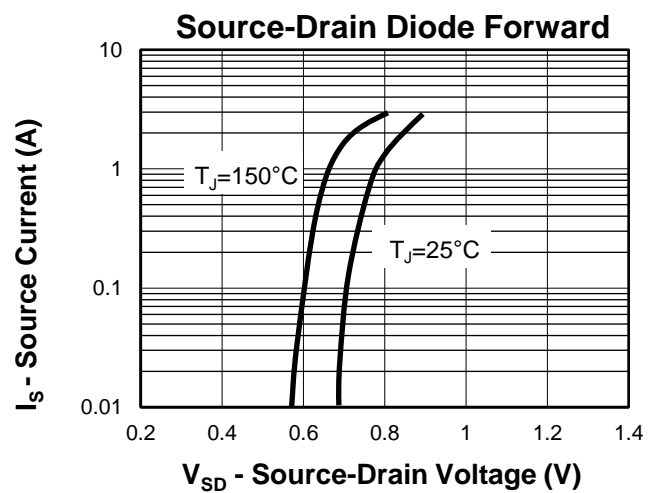
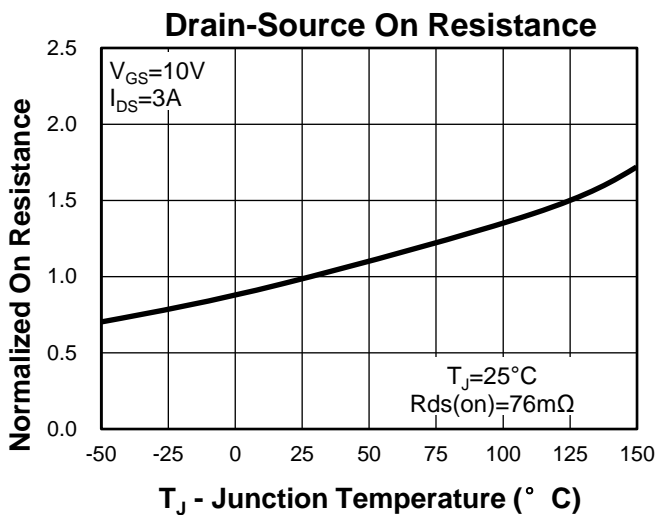
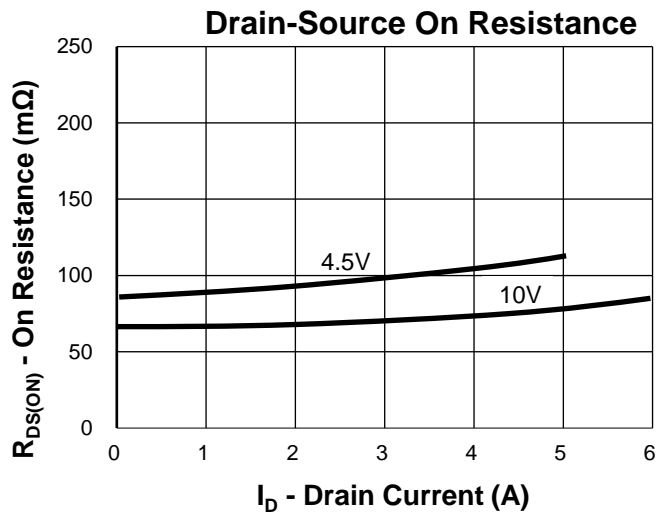
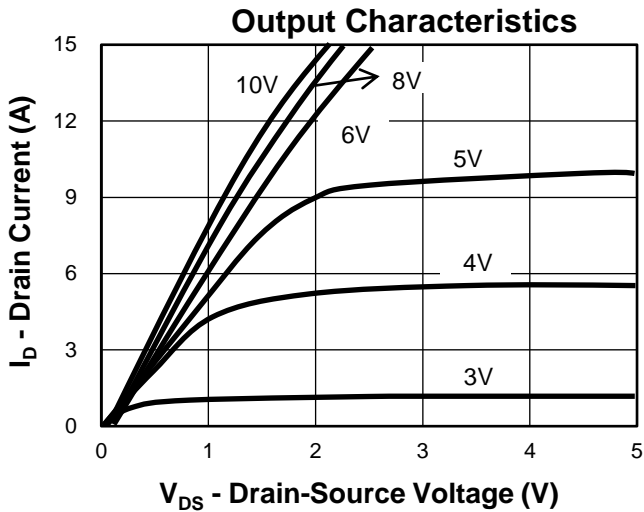
### Typical Characteristics

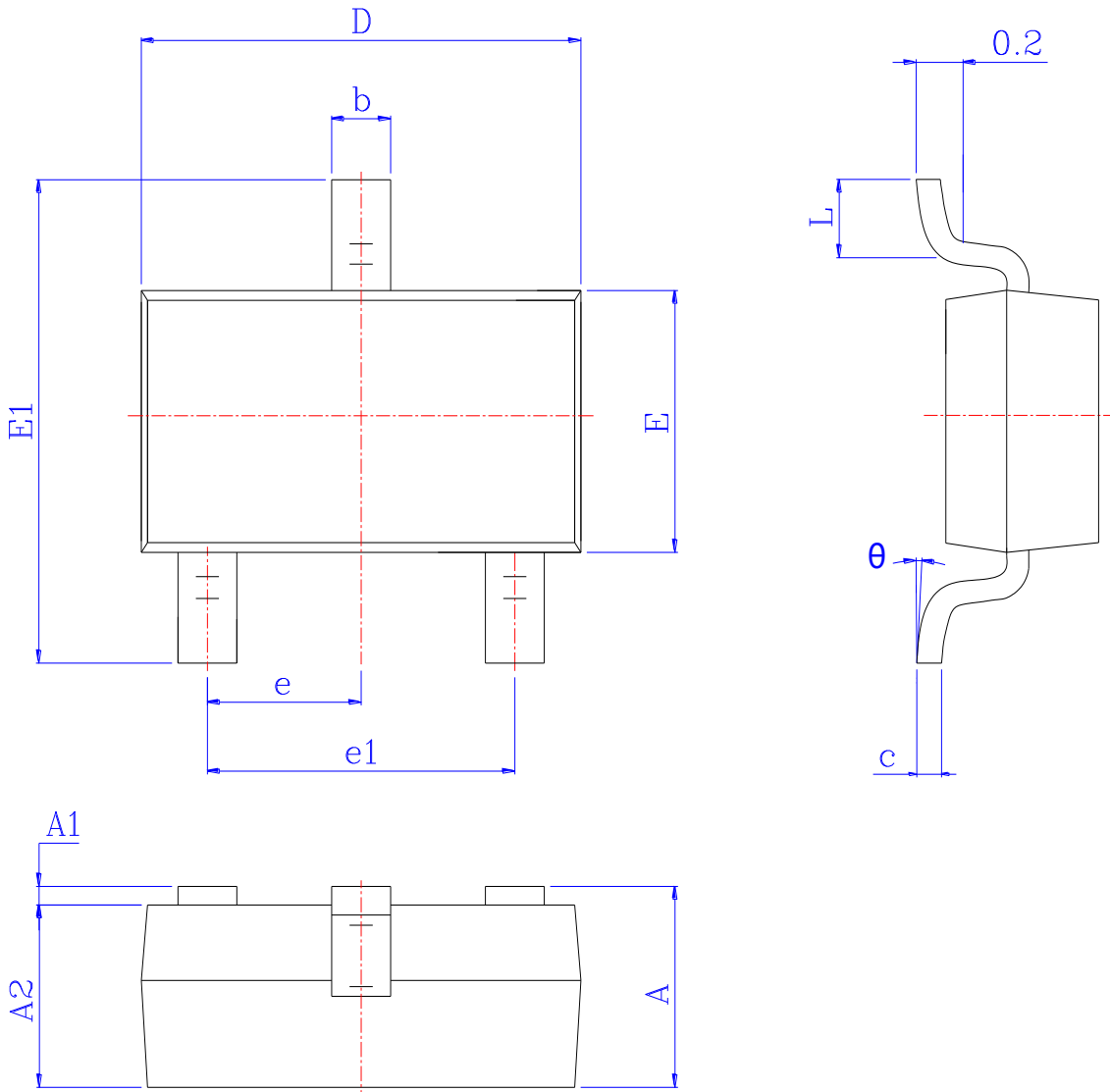


### Thermal Transient Impedance



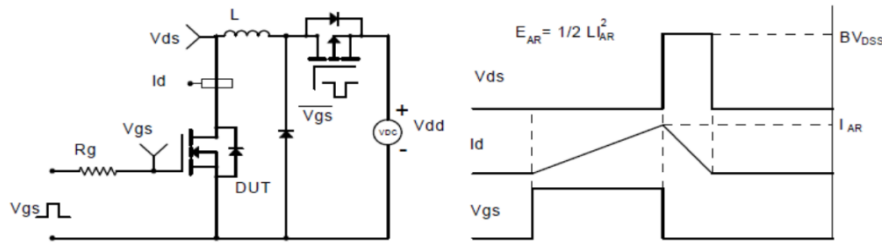
Typical Characteristics



**Package Information**
**SOT23-3L**


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.950	1.150	1.450	0.037	0.045	0.057
A1	0.000	*	0.150	0.000	*	0.006
A2	0.900	1.100	1.300	0.035	0.043	0.051
b	0.300	0.400	0.500	0.012	0.016	0.020
c	0.080	0.150	0.200	0.003	0.006	0.008
D	2.800	2.925	3.050	0.110	0.115	0.120
E	1.500	1.600	1.750	0.059	0.063	0.069
E1	2.650	2.800	3.000	0.104	0.110	0.118
e	0.950 BSC			0.037 BSC		
e1	1.800	1.900	2.000	0.071	0.075	0.079
L	0.300	0.450	0.600	0.012	0.018	0.024
θ	0°	4°	8°	0°	4°	8°

### Avalanche Test Circuit and Waveforms



### Switching Time Test Circuit and Waveforms



### Diode Recovery Test Circuit and Waveforms



### Gate Charge Test Circuit and Waveform



### Customer Service

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